

Features

- Trench LV MOSFET Technology
- High Density Cell Design For Low $R_{DS(ON)}$
- Moisture Sencitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

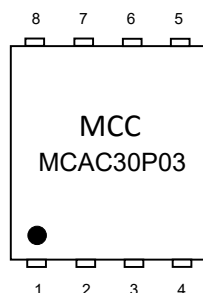
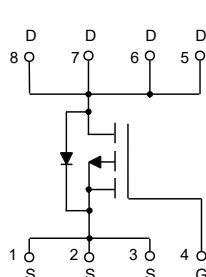
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 50°C/W Junction to Ambient (Note 2)
- Thermal Resistance: 3°C/W Junction to Case

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V _{DS}	-30	V
Gate-Source Voltlage		V _{GS}	±20	V
Continuous Drain Current	T _C =25°C	I _D	-30	A
	T _C =100°C		-19	
Pulsed Drain Current ^(Note 3)		I _{DM}	-120	A
Total Power Dissipation ^(Note 4)		P _D	41.7	W
Single Pulsed Avalanche Energy ^(Note 5)		E _{AS}	60	mJ

Note:

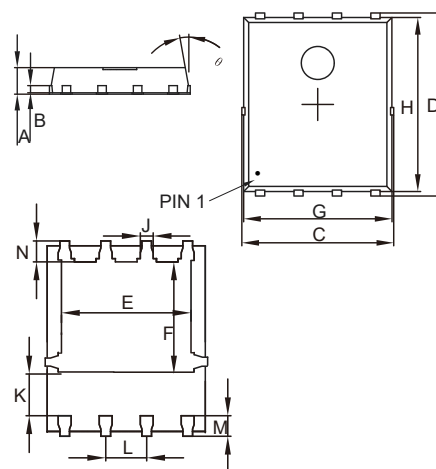
1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-case thermal resistance.
5. $T_J = 25^\circ\text{C}$, $V_{DD} = -30\text{V}$, $V_{GS} = -10\text{V}$, $R_G = 25\Omega$, $L = 1\text{mH}$.

Internal Structure and Marking Code



P-CHANNEL MOSFET

DFN5060



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.031	0.047	0.80	1.20	
B	0.010		0.254		TYP.
C	0.193	0.222	4.90	5.64	
D	0.232	0.250	5.90	6.35	
E	0.148	0.167	3.75	4.25	
F	0.126	0.154	3.20	3.92	
G	0.189	0.213	4.80	5.40	
H	0.222	0.239	5.65	6.06	
K	0.045	0.059	1.15	1.50	
J	0.012	0.020	0.30	0.50	
L	0.046	0.054	1.17	1.37	
M	0.012	0.028	0.30	0.71	
N	0.016	0.028	0.40	0.71	

Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250μA	-30			V
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V			-1	μA
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1	-1.5	-2	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-20A		12.4	16	mΩ
		V _{GS} =-4.5V, I _D =-20A		17.9	25	
Gate Resistance	R _g	f=1 MHz, Open drain		5		Ω
Diode Characteristics						
Continuous Body Diode Current	I _S				-25	A
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-20A			-1.2	V
Reverse Recovery Time	t _{rr}	I _F =-20A, dI _F /dt=100A/μs		20		ns
Reverse Recovery Charge	Q _{rr}			9		nC
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =-15V,V _{GS} =0V,f=1MHz		1385		pF
Output Capacitance	C _{oss}			169		
Reverse Transfer Capacitance	C _{rss}			151		
Total Gate Charge	Q _g	V _{DS} =-15V,V _{GS} =-10V,I _D =-20A		28		nC
Gate-Source Charge	Q _{gs}			3.9		
Gate-Drain Charge	Q _{gd}			6		
Turn-On Delay Time	t _{d(on)}	V _{DD} =-20V, V _{GS} =-10V, R _G =2.5Ω, I _{DS} =-20A		8.2		ns
Turn-On Rise Time	t _r			11		
Turn-Off Delay Time	t _{d(off)}			41		
Turn-Off Fall Time	t _f			22		

Curve Characteristics

Fig. 1 - Typical Output Characteristics

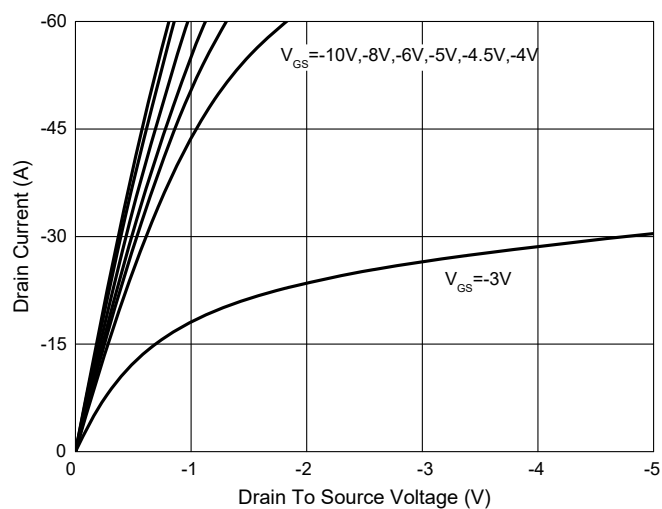


Fig. 2 - Transfer Characteristics

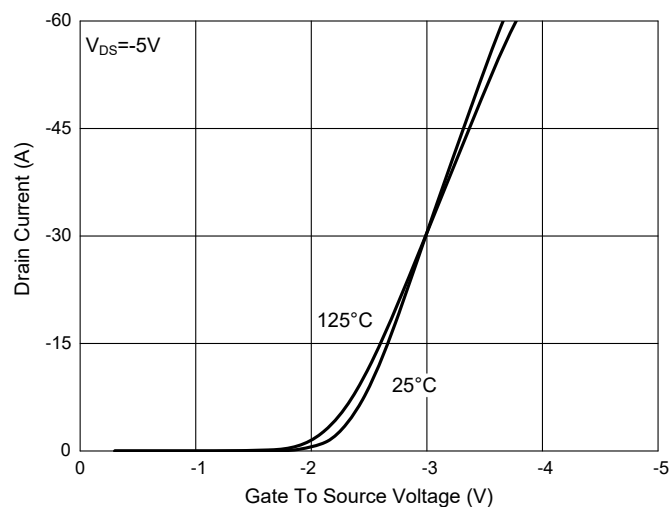


Fig. 3 - $R_{DS(ON)} - V_{GS}$

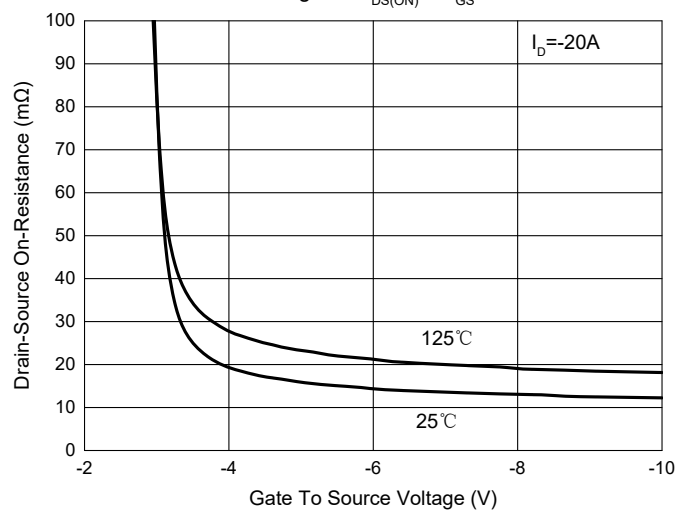


Fig. 4 - $R_{DS(ON)} - I_D$

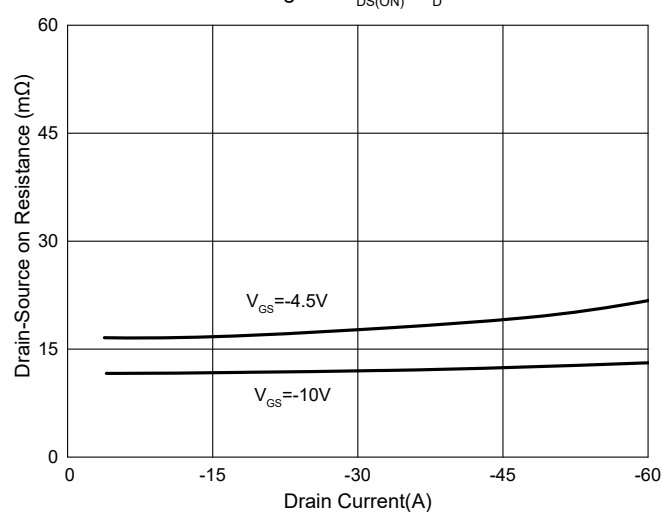


Fig. 5 - Capacitance Characteristics

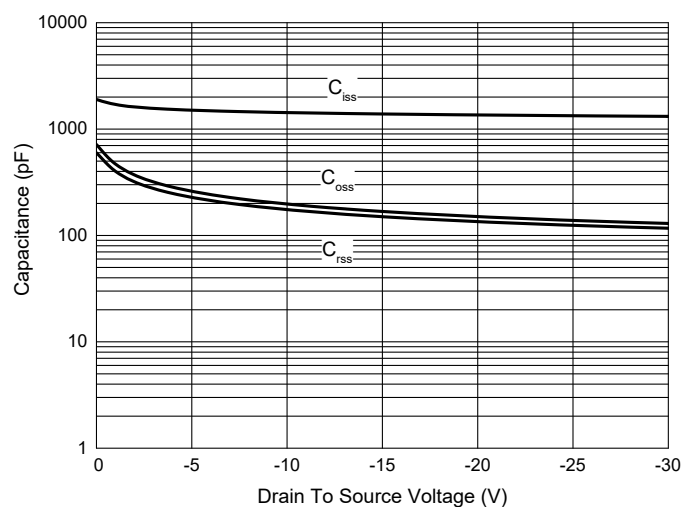
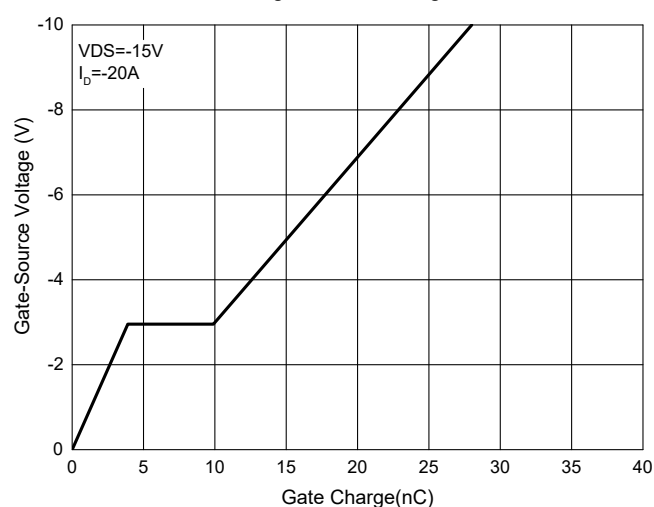


Fig. 6 - Gate Charge



Curve Characteristics

Fig. 7 - Normalized Threshold voltage

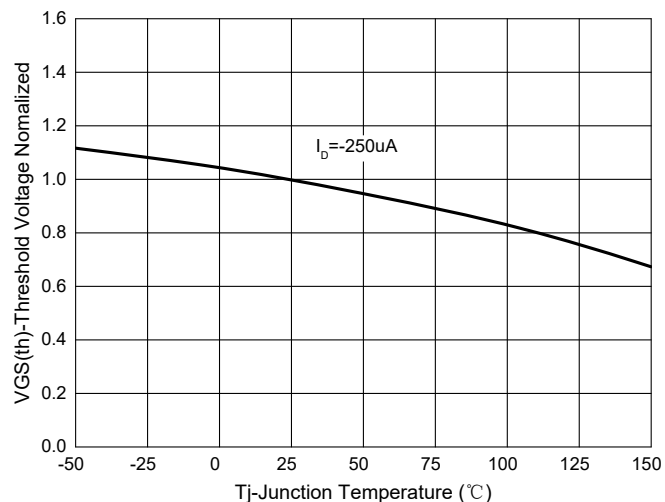


Fig.8-Normalized On Resistance Characteristics

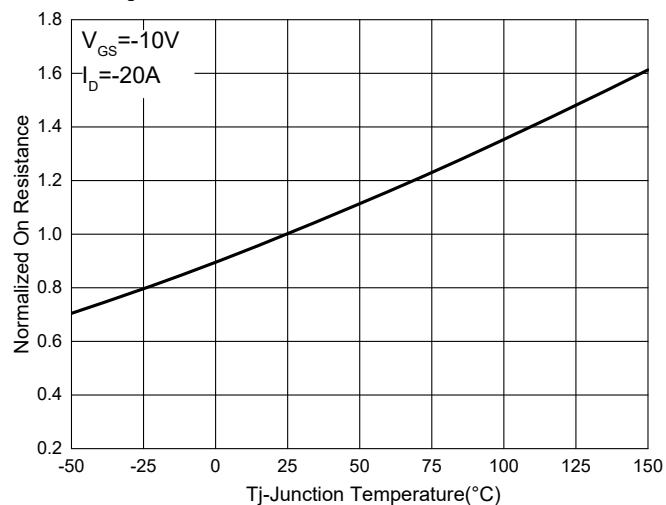


Fig. 9 - $I_S - V_{SD}$

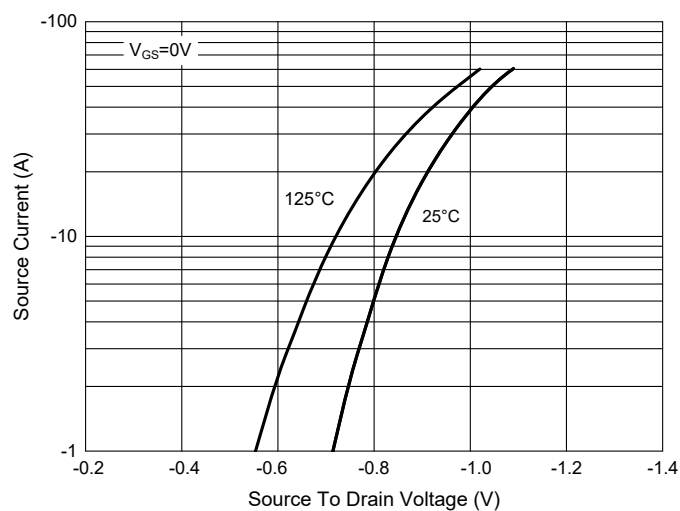


Fig. 10 - Drain Current

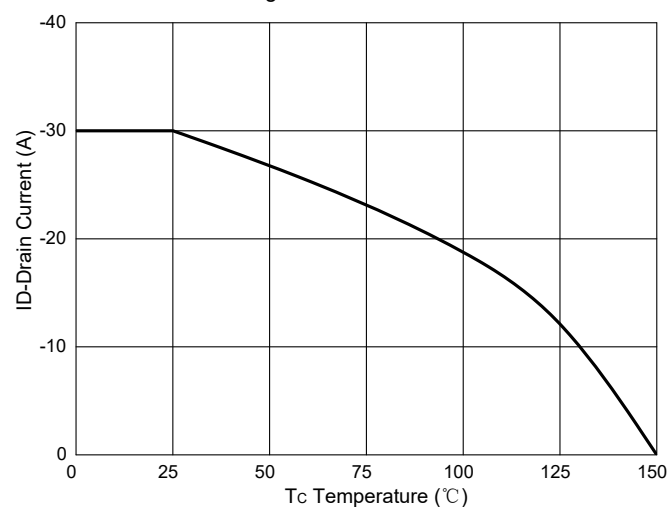
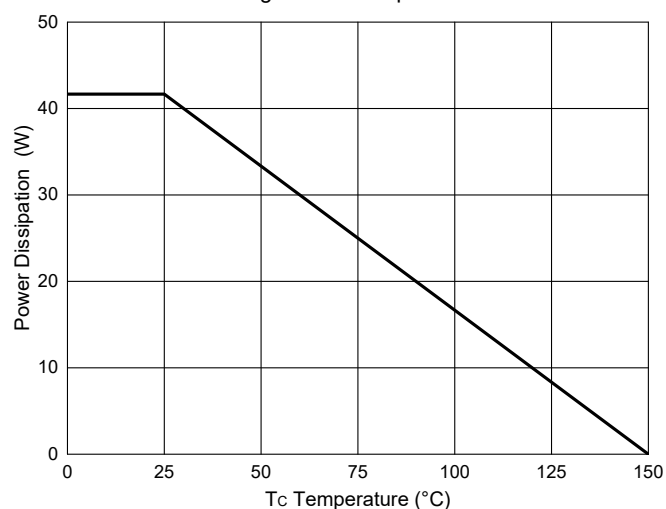


Fig.11-PD Dissipation



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel

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